Ordering number : ENA1604A

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

P-Channel Silicon MOSFET

ATP108 — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Slim package
- Halogen free compliance
- Large current
- 4.5V drive
- Protection diode in

Specifications

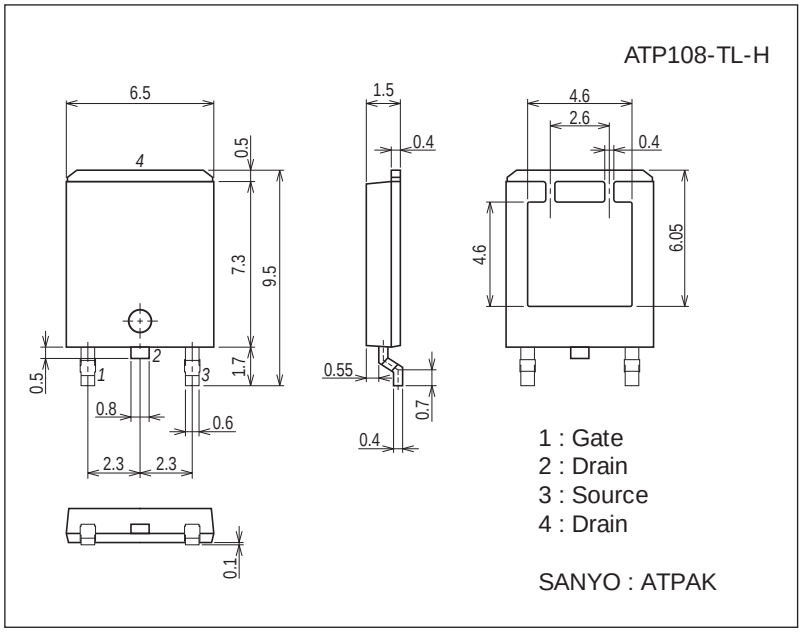
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		−40	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		−70	A
Drain Current (PW≤10μs)	I_{DP}	PW≤10μs, duty cycle≤1%	−210	A
Allowable Power Dissipation	P_D	Tc=25°C	60	W
Channel Temperature	Tch		150	℃
Storage Temperature	Tstg		−55 to +150	℃
Avalanche Energy (Single Pulse) *1	E_{AS}		95	mJ
Avalanche Current *2	I_{AV}		−35	A

Note :*1 V_{DD}=−15V, L=100μH, I_{AV}=−35A
*2 L≤100μH, Single pulse

Package Dimensions

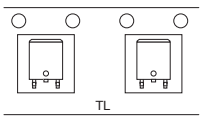
unit : mm (typ)
7057-001



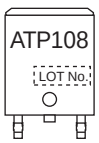
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

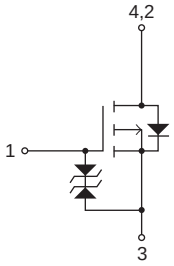
Packing Type: TL



Marking



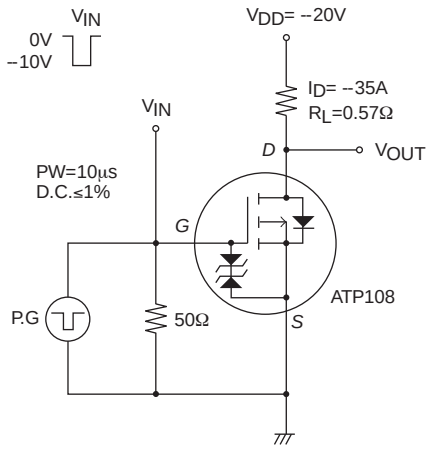
Electrical Connection



Electrical Characteristics at Ta=25°C

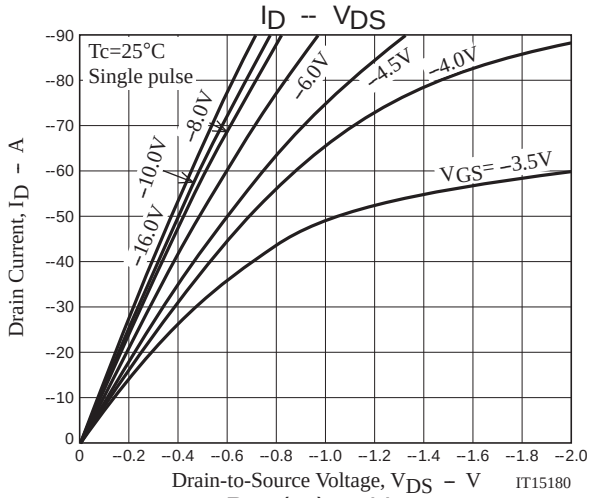
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=−1mA, V_{GS}=0V	−40			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=−40V, V_{GS}=0V			−1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=−10V, I_D=−1mA	−1.5		−2.6	V
Forward Transfer Admittance	| yfs |	V_{DS}=−10V, I_D=−35A		65		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=−35A, V_{GS}=−10V		8	10.4	mΩ
	R_{DS}(on)2	I_D=−18A, V_{GS}=−4.5V		11.5	16.5	mΩ
Input Capacitance	Ciss	V_{DS}=−20V, f=1MHz		3850		pF
Output Capacitance	Coss			560		pF
Reverse Transfer Capacitance	Crss			390		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		19		ns
Rise Time	t_r			340		ns
Turn-OFF Delay Time	t_d(off)			340		ns
Fall Time	t_f			290		ns
Total Gate Charge	Qg	V_{DS}=−20V, V_{GS}=−10V, I_D=−70A		79.5		nC
Gate-to-Source Charge	Qgs			20		nC
Gate-to-Drain “Miller” Charge	Qgd			15		nC
Diode Forward Voltage	V_{SD}	I_S=−70A, V_{GS}=0V		−1.05	−1.5	V

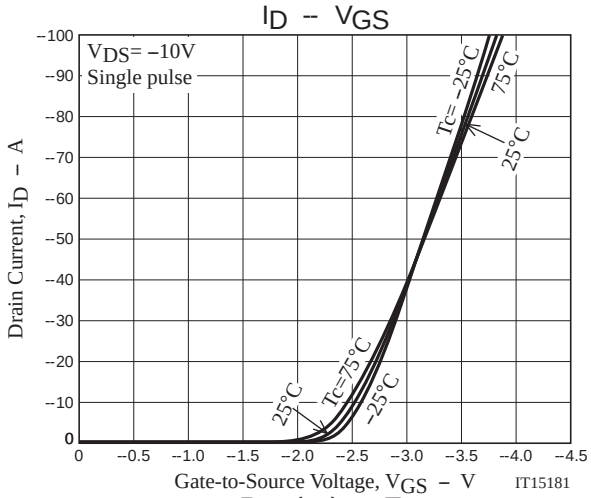
Switching Time Test Circuit

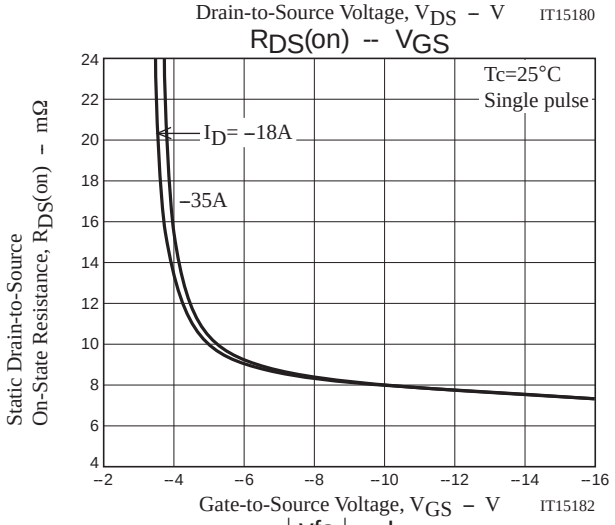


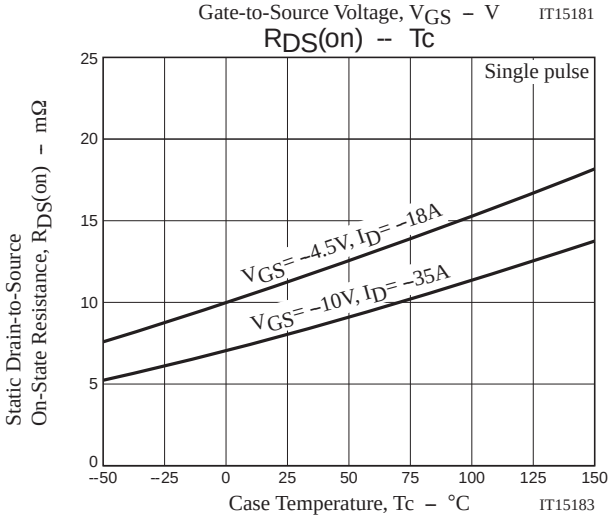
Ordering Information

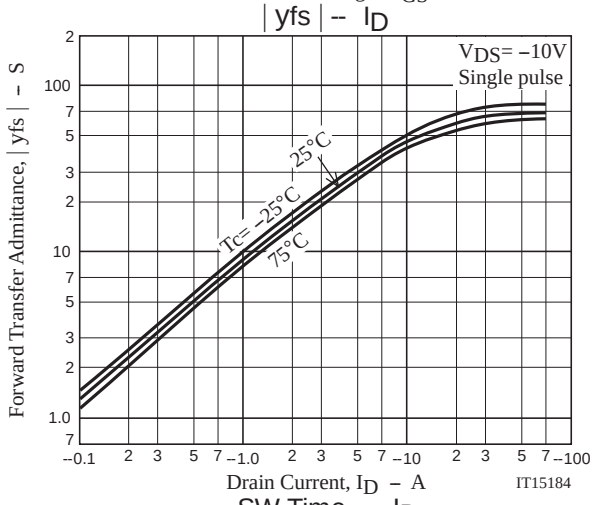
Device	Package	Shipping	memo
ATP108-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free

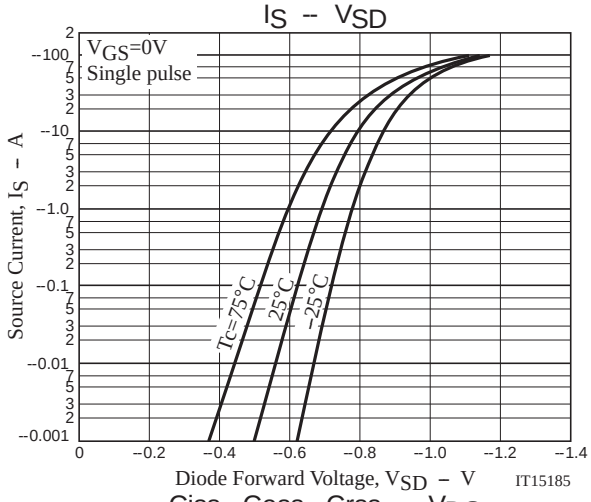

I_D -- V_{DS}
Tc=25°C
Single pulse
−8.0V
−6.0V
−4.5V
−4.0V
−10.0V
−16.0V
VGS= −3.5V
Drain Current, ID − A
Drain-to-Source Voltage, VDS − V
IT15180

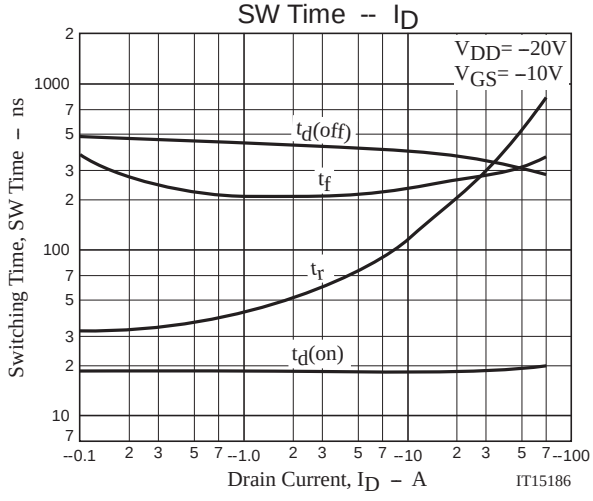

I_D -- V_{GS}
VDS= −10V
Single pulse
Tc= −25°C
75°C
25°C
Drain Current, ID − A
Gate-to-Source Voltage, VGS − V
IT15181

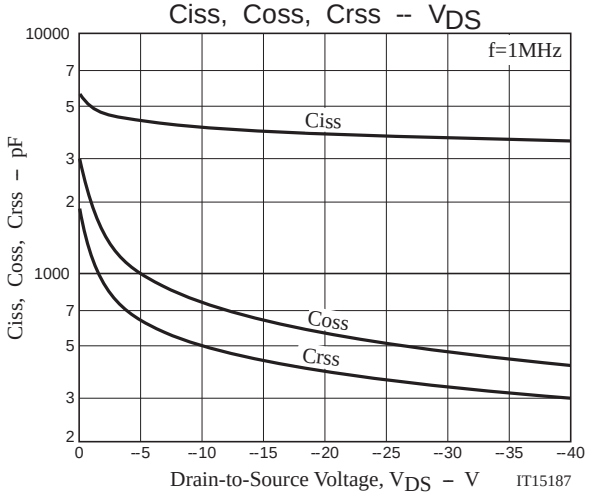

$R_{DS(on)}$ -- V_{GS}
Tc=25°C
Single pulse
ID= −18A
−35A
Static Drain-to-Source On-State Resistance, RDS(on) − mΩ
Gate-to-Source Voltage, VGS − V
IT15182

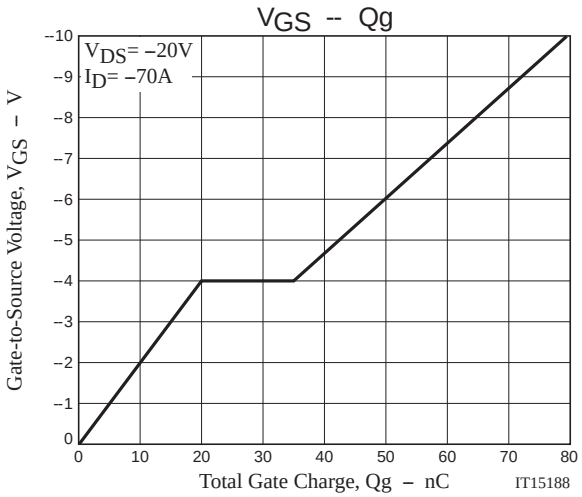

$R_{DS(on)}$ -- Tc
Single pulse
VGS= −4.5V, ID= −18A
VGS= −10V, ID= −35A
Static Drain-to-Source On-State Resistance, RDS(on) − mΩ
Case Temperature, Tc − °C
IT15183

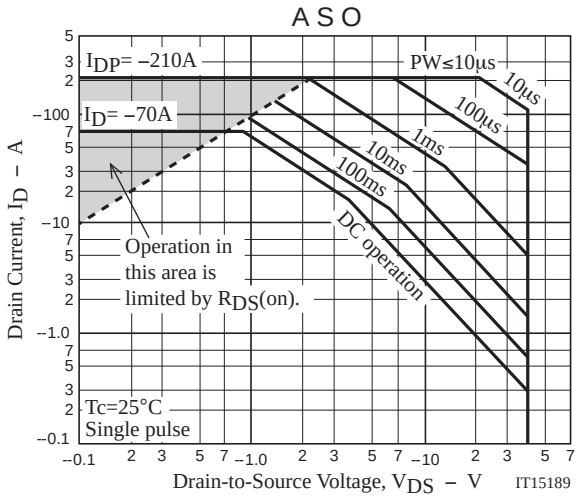

| yfs | -- I_D
VDS= −10V
Single pulse
25°C
Tc= −25°C
75°C
Forward Transfer Admittance, | yfs | − S
Drain Current, ID − A
IT15184

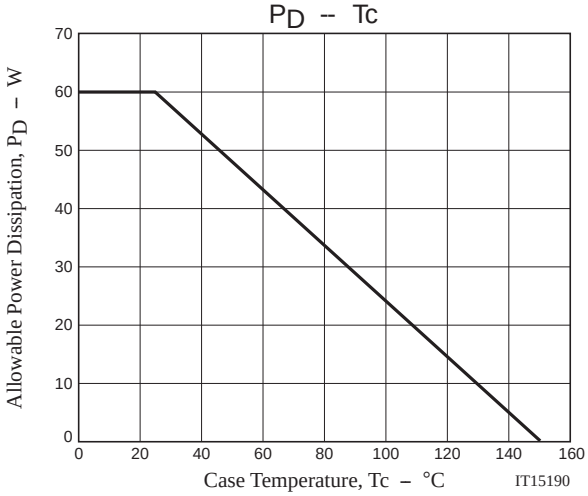

I_S -- V_{SD}
VGS=0V
Single pulse
Tc=75°C
25°C
−25°C
Source Current, IS − A
Diode Forward Voltage, VSD − V
IT15185

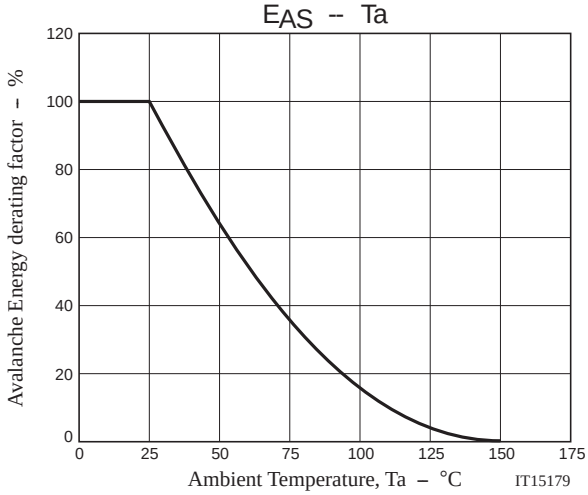

SW Time -- I_D
VDD= −20V
VGS= −10V
td(off)
tf
tr
td(on)
Switching Time, SW Time − ns
Drain Current, ID − A
IT15186


Ciss, Coss, Crss -- V_{DS}
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss − pF
Drain-to-Source Voltage, VDS − V
IT15187


VGS -- Qg
VDS= −20V
ID= −70A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT15188


A S O
IDP= −210A
PW≤10μs
10μs
100μs
1ms
10ms
100ms
DC operation
ID= −70A
Operation in this area is limited by RDS(on).
Tc=25°C
Single pulse
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT15189


PD -- Tc
Allowable Power Dissipation, PD – W
Case Temperature, Tc – °C
IT15190


EAS -- Ta
Avalanche Energy derating factor – %
Ambient Temperature, Ta – °C
IT15179

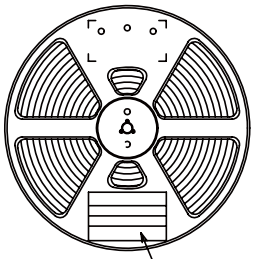
Taping Specification

ATP108-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

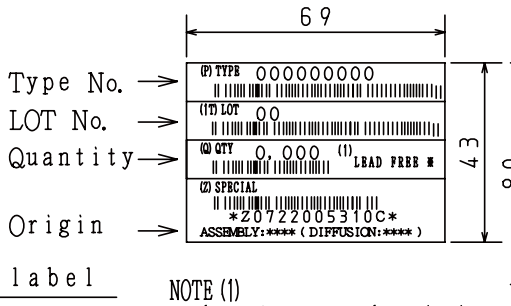
Packing method



Reel label

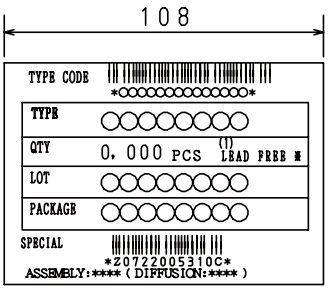
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



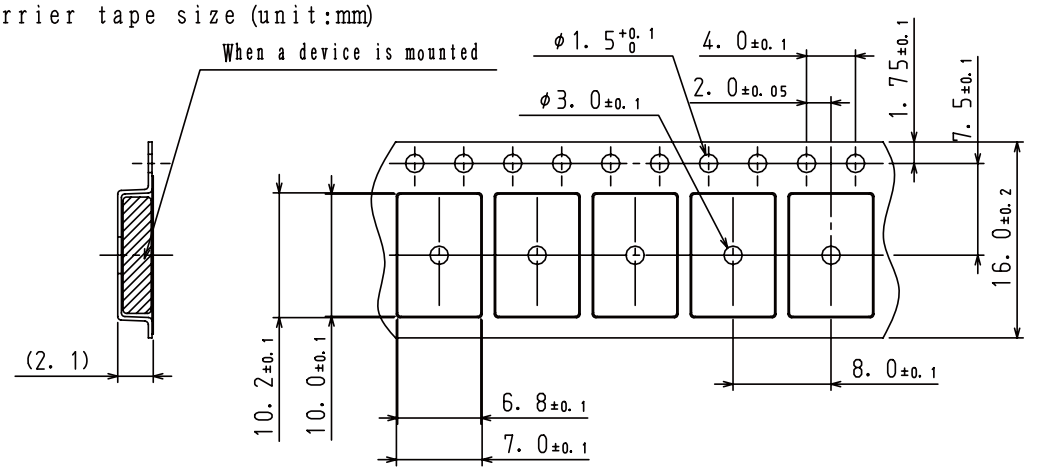
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

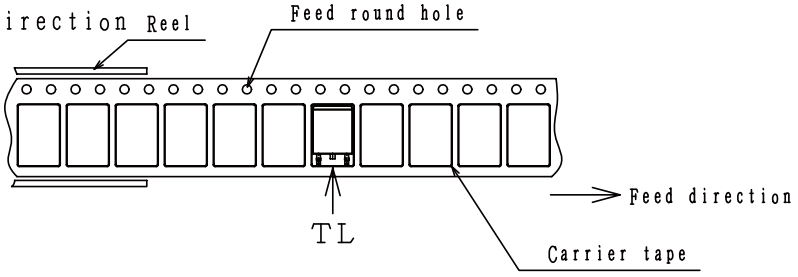
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



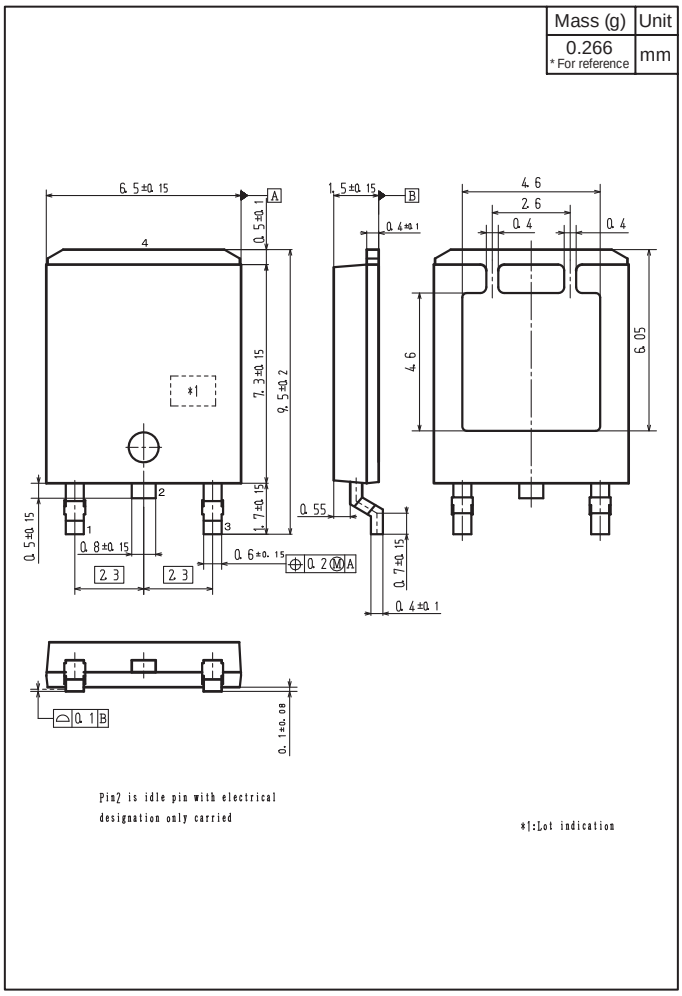
2-2. Device placement direction



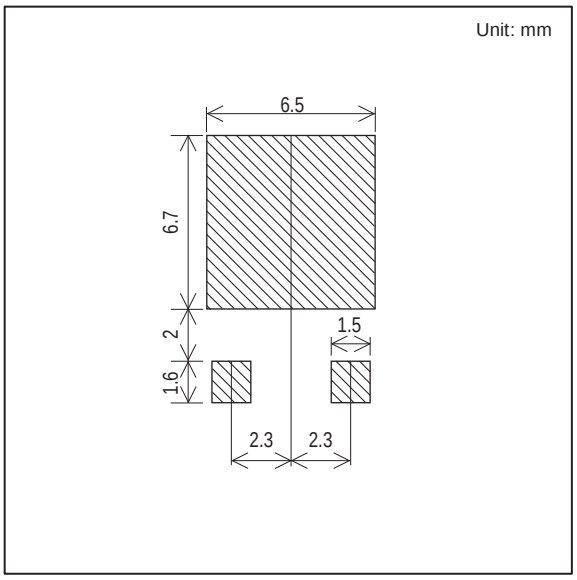
The one erectrode terminals on feed hole side····TL

Outline Drawing

ATP108-TL-H



Land Pattern Example



Note on usage : Since the ATP108 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.